

Session Program

25-28 Jun 2006

8th RD50 Workshop

New Materials

Prague

Wednesday 28 June

09:00

New Materials

Session | Location: Prague

09:00-09:20

I-V & CCE results of neutron irradiated GaN Schottky Detectors

Speaker

James Grant

09:20-09:40

Properties of irradiated semi-insulating GaN

Speaker

Juozas Vaitkus

09:40-10:00

KINETICS OF INTERSTITIAL CARBON ANNEALING AND MONITORING OF OXYGEN DISTRIBUTION IN SILICON PARTICLE DETECTORS

Speaker

Leonid Makarenko

10:00-10:20

CHARACTERIZATION OF DEFECTS WITH SMALL CAPTURE CROSS-SECTION IN DETECTOR-GRADE SILICON BY DLTS and LAPLACE-DLTS

Speaker

Leonid Makarenko

10:20-10:50

coffee break

10:50-11:10

Annealing of the vacancy-oxygen and divacancy-oxygen complexes in silicon

Speaker

Eduard Monakhov

11:10-11:30

The influence of growth conditions on irradiation induced defects in 4H-SiC

Speaker

Ioana Pintilie

11:30-11:50

Deep levels induced by very high dose neutron irradiation in 4H-SiC

Speaker

Filippo Fabbri

11:50-12:10

Annealing effects on p+n junction 4H-SiC diodes after very high neutron irradiation

Speaker

Francesco Moscatelli

12:10-12:40

Discussion session on New Materials

12:40